

N-channel TrenchMOS SiliconMAX standard level FET 15 August 2013 Product data sheet

### 1. General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

#### 2. Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

### 3. Applications

- DC-to-DC converters
- Switched-mode power supplies

### 4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	200	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C		-	-	39	А
P <sub>tot</sub>	total power dissipation			-	-	250	W
Static chara	cteristics	·					
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 17 A; T <sub>j</sub> = 25 °C		-	41	57	mΩ
Dynamic ch	aracteristics	·	1	1			
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; I <sub>D</sub> = 39 A; V <sub>DS</sub> = 160 V; T <sub>j</sub> = 25 °C		-	37	50	nC



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### 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

## 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN057-200B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

#### 7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN057-200B	PSMN057-200B

### 8. Limiting values

#### Table 5. Limiting values

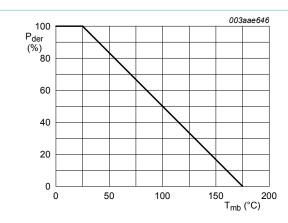
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	200	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	200	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 100 °C	-	27.5	А
		T <sub>mb</sub> = 25 °C	-	39	А
I <sub>DM</sub>	peak drain current	pulsed; T <sub>mb</sub> = 25 °C	-	156	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C	-	250	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
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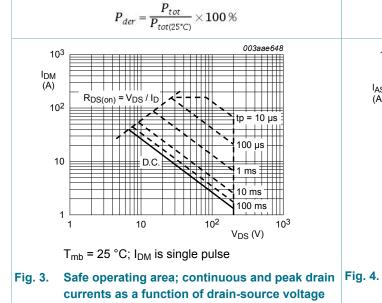
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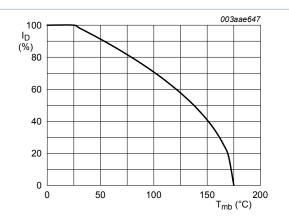
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Symbol	Parameter	Conditions	Min	Max	Unit
Source-dra	in diode	· · · · · · · · · · · · · · · · · · ·		_	
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	39	А
I <sub>SM</sub>	peak source current	pulsed; T <sub>mb</sub> = 25 °C	-	156	А
Avalanche	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{aligned} &V_{GS} \texttt{=} 10 \; V; \; T_{j(init)} \texttt{=} 25 \; ^\circ C; \; I_{D} \texttt{=} 35 \; A; \\ &V_{sup} \texttt{\leq} 50 \; V; \; unclamped; \; t_{p} \texttt{=} 100 \; \mu s; \\ &R_{GS} \texttt{=} 50 \; \Omega \end{aligned} $	-	300	mJ
I <sub>AS</sub>	non-repetitive avalanche current		-	35	A

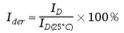


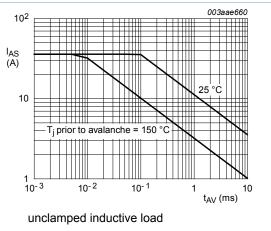
# Fig. 1. Normalized total power dissipation as a function of mounting base temperature





# Fig. 2. Normalized continuous drain current as a function of mounting base temperature





J. 4. Single-shot avalanche rating; avalanche current as a function of avalanche period

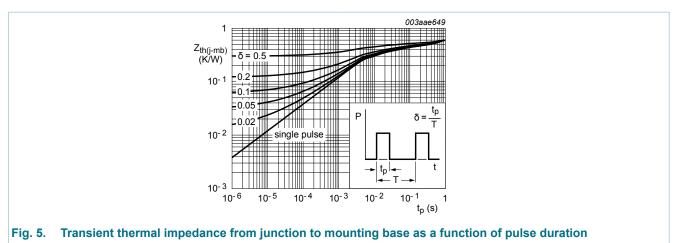
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### 9. Thermal characteristics

Table 6. Thermal characteristics							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base			-	-	0.6	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; FR4 board		-	50	-	K/W



### 10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	· · ·				
V <sub>(BR)DSS</sub>	drain-source	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	200	-	-	V
breakdown voltage	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = -55 °C	178	-	-	V	
V <sub>GS(th)</sub> gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C	1	-	-	V	
	voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	4.4	V
I <sub>DSS</sub> drain leakage of	drain leakage current	$V_{DS}$ = 200 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
		$V_{DS}$ = 200 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	0.03	10	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 17 A; T <sub>j</sub> = 175 °C	-	-	165	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 17 A; T <sub>i</sub> = 25 °C	-	41	57	mΩ

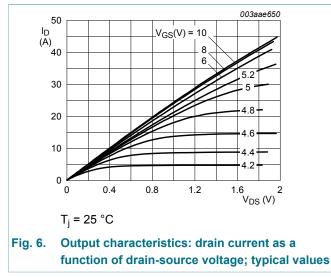
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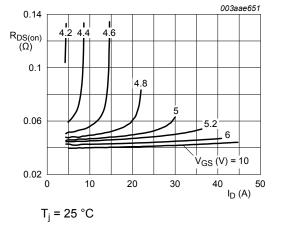
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	2	4.1	Ω
Dynamic ch	naracteristics	· · ·		I		
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 39 A; $V_{DS}$ = 160 V; $V_{GS}$ = 10 V;	-	96	135	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	13	-	nC
Q <sub>GD</sub>	gate-drain charge		-	37	50	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	3750	5036	pF
C <sub>oss</sub>	output capacitance		-	385	520	pF
C <sub>rss</sub>	reverse transfer capacitance		-	180	252	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 100 V; R <sub>L</sub> = 2.7 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5.6 Ω; T <sub>j</sub> = 25 °C	-	18	-	ns
t <sub>r</sub>	rise time		-	58	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	105	-	ns
t <sub>f</sub>	fall time		-	78	-	ns
L <sub>D</sub>	internal drain inductance	measured from tab to centre of die ; $T_j = 25 \ ^\circ C$	-	3.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-dra	in diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S}$ = 20 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V;	-	133	173	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 30 V; T <sub>j</sub> = 25 °C	-	895	-	nC





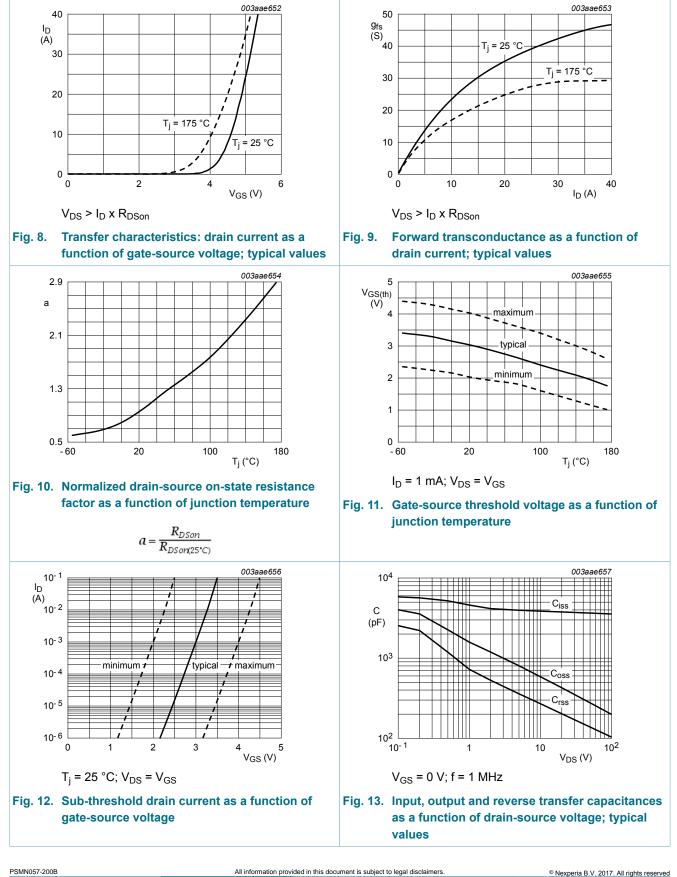


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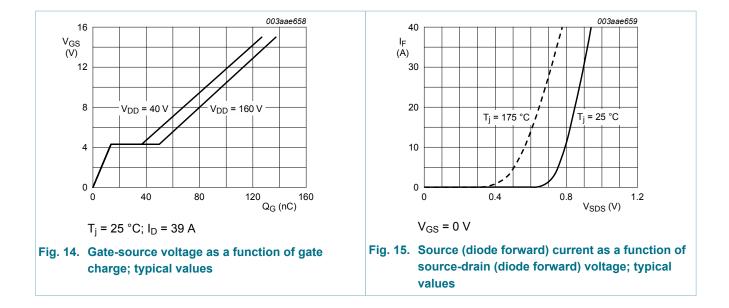
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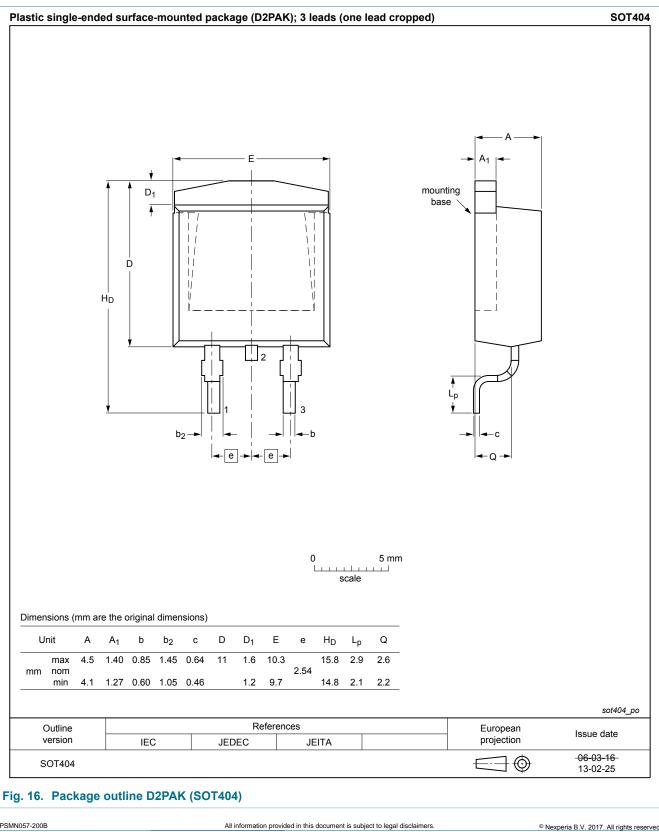


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### 11. Package outline



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#### 12. Legal information

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Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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